

**Silicon NPN Power Transistors**

**2SC1046**

**DESCRIPTION**

- With TO-3 package
- High breakdown voltage

**APPLICATIONS**

- For CRT horizontal output applications

**PINNING(see fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

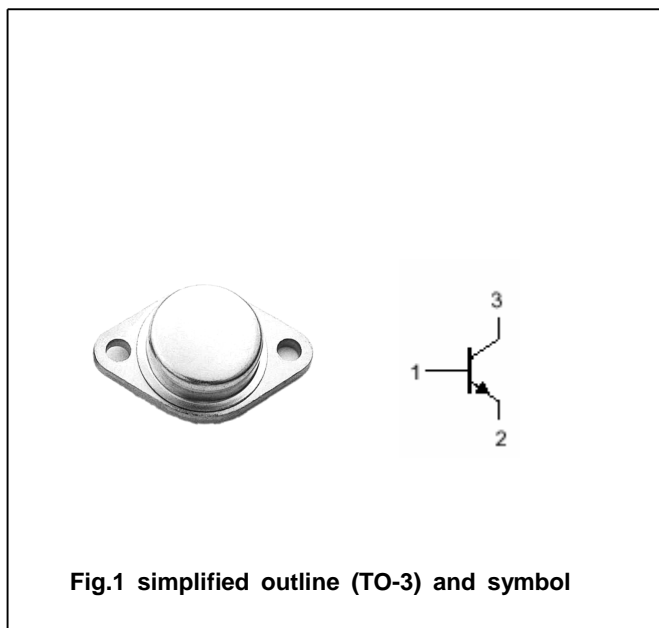


Fig.1 simplified outline (TO-3) and symbol

**Absolute maximum ratings(Ta=?)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1000	V
$V_{CEO}$	Collector-emitter voltage	Open base	400	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		3	A
$P_C$	Collector power dissipation	$T_C=25^\circ$	25	W
$T_j$	Junction temperature		125	?
$T_{stg}$	Storage temperature		-40~125	?

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## 2SC1046

## CHARACTERISTICS

T<sub>j</sub>=25° unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =5mA; I <sub>B</sub> =0	400			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA; I <sub>E</sub> =0	1000			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2 A; I <sub>B</sub> =0.4A			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =800V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2 A ; V <sub>CE</sub> =5V	4		20	

PACKAGE OUTLINE

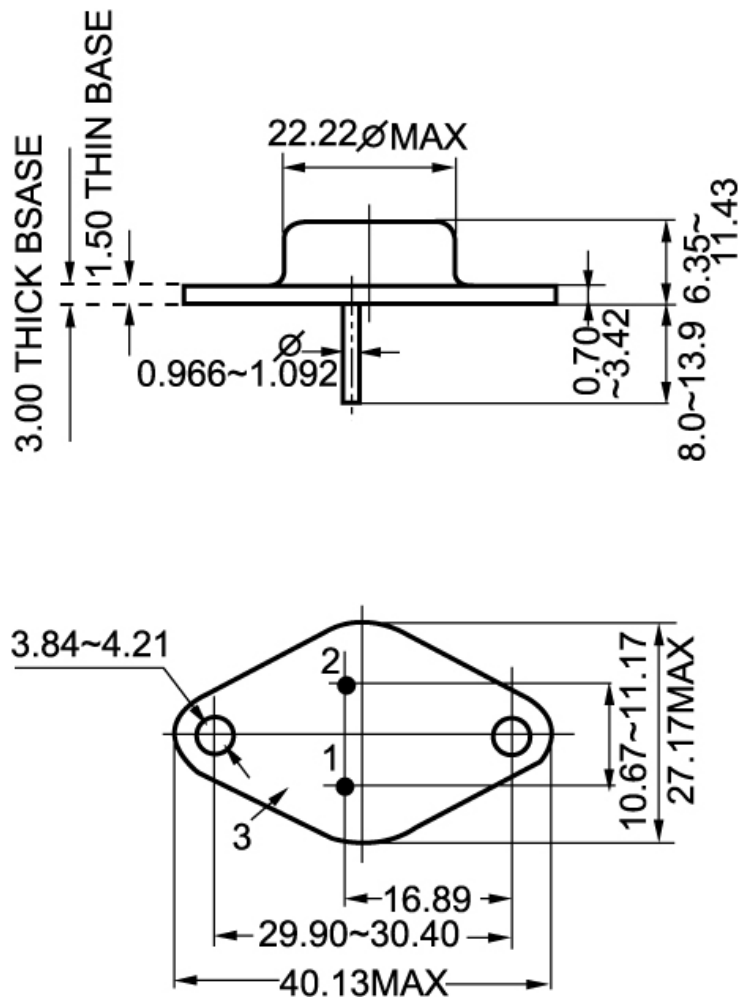


Fig.2 Outline dimensions